

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
60V	0.04Ω @ V _{GS} = 10V	7.5A
00 V	0.06Ω @ V _{GS} = 4.5V	6.2A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMN6A09GQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

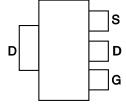
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.112 grams (Approximate)

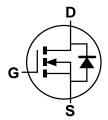
SOT223



Top View



Pin Out - Top View



Equivalent Circuit

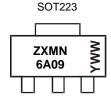
Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN6A09GQTA	SOT223	1,000/ Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



ZXMN6A09 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 9 = 2019) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

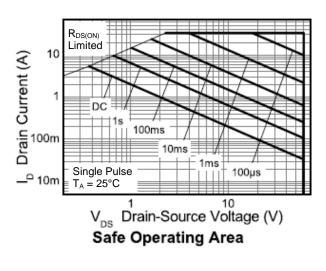
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current $@V_{GS} = 10V$; $T_A = +25^{\circ}C$ (Note 6) $@V_{GS} = 10V$; $T_A = +70^{\circ}C$ (Note 6) $@V_{GS} = 10V$; $T_A = +25^{\circ}C$ (Note 5)	I _D	7.5 6 5.4	А
Pulsed Drain Current (Note 7)	I _{DM}	33	Α
Continuous Source Current (Body Diode) (Note 6)	Is	3.5	Α
Pulsed Source Current (Body Diode) (Note 7)	I _{SM}	33	А
Avalanche Current, L = 0.1mH	I _{AS}	1.17	Α
Avalanche Energy, L = 0.1mH	E _{AS}	0.07	mJ

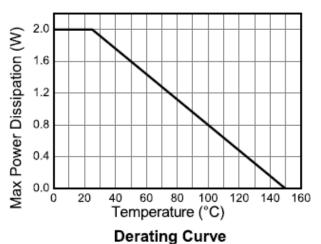
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

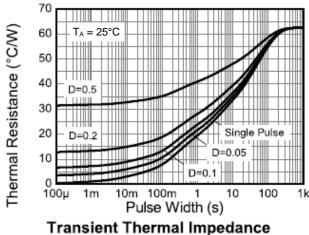
Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5) Linear Derating Factor	P _D	2.0 16	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	32.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

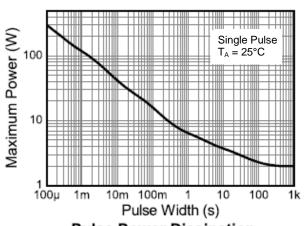
Notes: 5. For a device surface mounted on 25mm × 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

^{7.} Repetitive rating $25mm \times 25mm$ FR-4 PCB, D = 0.02 pulse width = $300\mu s$ - pulse width limited by maximum junction temperature.









Pulse Power Dissipation

^{6.} For a device surface mounted on FR-4 PCB measured at $t \le 10s$.



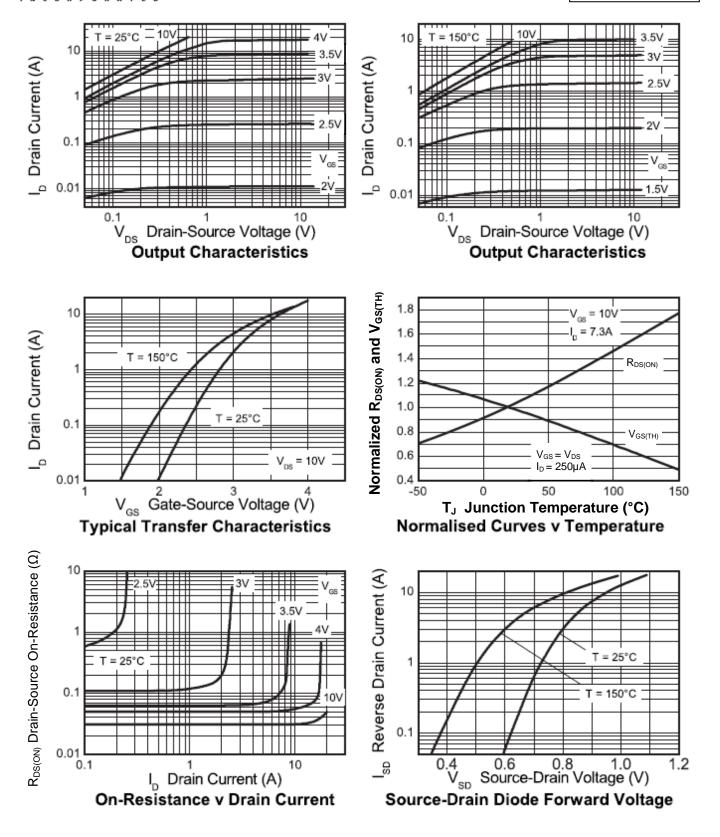
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance (Note 8)	В	_	0.02	0.04	Ω	$V_{GS} = 10V, I_D = 8.2A$	
Static Dialii-Source Off-Resistance (Note 6)	R _{DS(ON)}	_	0.03	0.06	Ω	$V_{GS} = 4.5V, I_D = 7.4A$	
Diode Forward Voltage (Note 8)	V _{SD}	_	0.85	0.95	V	$I_S = 6.6A$, $V_{GS} = 0V$, $T_J = +25$ °C	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 10)	C _{iss}	_	1407	_	pF		
Output Capacitance (Note 10)	Coss	_	121	_	pF	$V_{DS} = 40V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance (Note 10)	C _{rss}	_	59	_	pF		
Total Gate Charge (Notes 9 & 10) V _{GS} = 5V	Q_g	_	12.4	_	nC		
Total Gate Charge (Notes 9 & 10) V _{GS} = 10V	Q_g	_	24.2	_	nC	V _{DS} = 15V I _D = 3.5A	
Gate-Source Charge (Notes 9 & 10)	Q _{gs}	_	5.2	_	nC		
Gate-Drain Charge (Notes 9 & 10)	Q_{gd}	_	3.5	_	nC		
Turn-On Delay Time (Notes 9 & 10)	t _{D(ON)}	_	4.9	_	ns	V _{DD} = 15V, I _D = 3.5A, V _{GS} = 5V	
Turn-On Rise Time (Notes 9 & 10)	t _R	_	5.0	_	ns		
Turn-Off Delay Time (Notes 9 & 10)	t _{D(OFF)}	_	25.3	_	ns		
Turn-Off Fall Time (Notes 9 & 10)	t _F	_	4.6	_	ns		
Reverse Recovery Time (Note 10)	t _{RR}	_	26.3	_	ns	$I_F = 3.5A$, di/dt = 100A/ μ s,	
Reverse Recovery Charge (Note 10)	Q _{RR}	_	26.6	_	nC	T _J = +25°C	

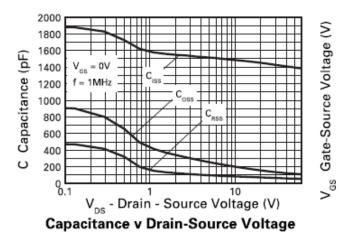
Notes:

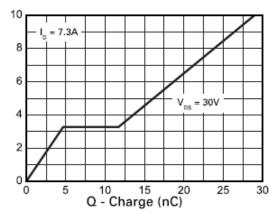
Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
Switching characteristics are independent of operating junction temperature.
For design aid only, not subject to production testing.



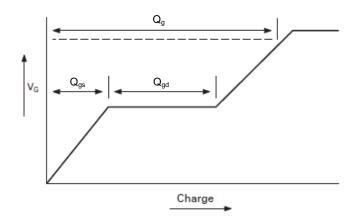


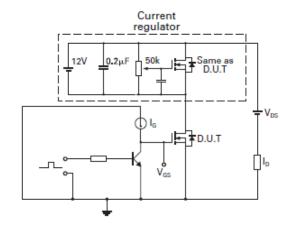






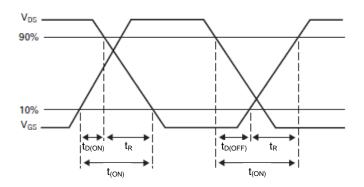
Gate-Source Voltage v Gate Charge

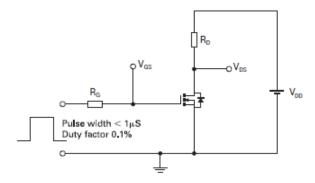




Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

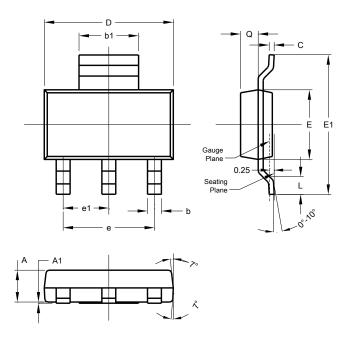
Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

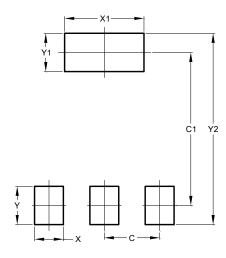


SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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